

GSB649A PNP EPITAXIAL PLANAR TRANSISTOR

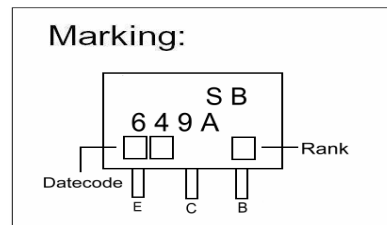
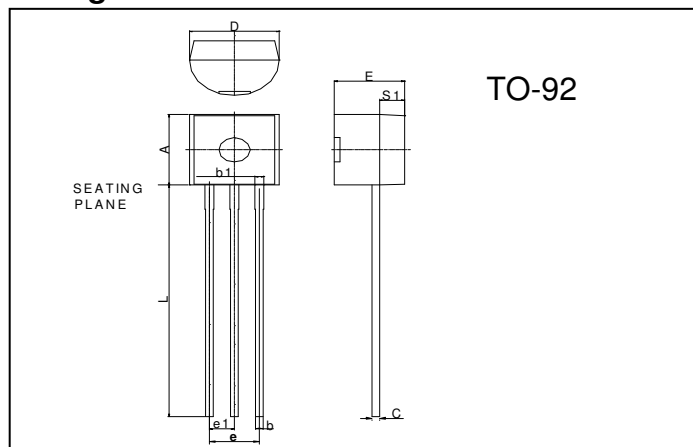
Description

The GSB649A is designed for frequency power amplifier.

Features

*Low frequency power amplifier Complementary pair with GSD669A

Package Dimensions



REF.	Millimeter		REF.	Millimeter	
	Min.	Max.		Min.	Max.
A	4.45	4.7	D	4.44	4.7
S1	1.02	-	E	3.30	3.81
b	0.36	0.51	L	12.70	-
b1	0.36	0.76	e1	1.150	1.390
C	0.36	0.51	e	2.42	2.66

Absolute Maximum Ratings (Ta = 25°C, unless otherwise specified)

Parameter		Ratings	Unit
Collector to Base Voltage	VCBO	-180	V
Collector to Emitter Voltage	VCEO	-160	V
Emitter to Base Voltage	VEBO	-5	V
Collect Current(DC)	IC	-1.5	A
Collect Current*(Pulse)	ICP	-3	A
Junction Temperature	Tj	+150	°C
Storage Temperature Range	Tstg	-55 ~ +150	°C
Total Power Dissipation	PD	1	W
Total Power Dissipation (TC=25°C)	PD	20	W

Electrical Characteristics (Ta = 25°C, unless otherwise specified)

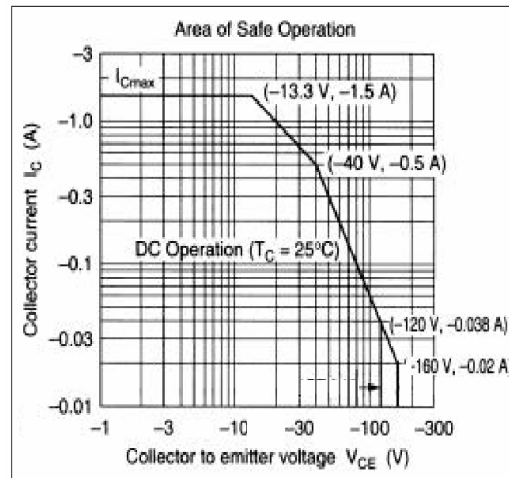
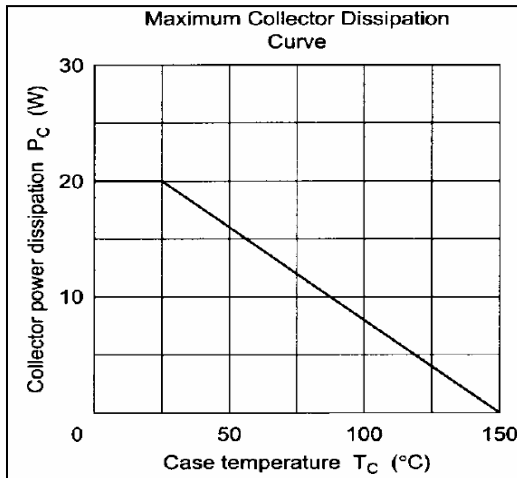
Symbol	Min.	Typ.	Max.	Unit	Test Conditions
V(BR)CBO	-180	-	-	V	IC=-1mA, IE=0
V(BR)CEO	-160	-	-	V	IC=-10mA, RBE=∞
V(BR)EBO	-5	-	-	V	IE=-1mA, IC=0
ICBO	-	-	-10	uA	VCB=-160V, IE=0
*VCE(sat)	-	-	-1	V	IC=-600mA, IB=-50mA
*VBE(on)	-	-	-1.5	V	VCE=-5V, IC=-150mA
*hFE1	60	-	200		VCE=-5V, IC=-150mA
*hFE2	30	-	-		VCE=-5V, IC=-500mA
fT	-	140	-	MHz	VCE=-5V, IC=-150mA
Cob	-	27	-	pF	VCB=-10V, IE=0, f=1MHz

* Pulse Test: Pulse Width ≤ 380us, Duty Cycle ≤ 2%

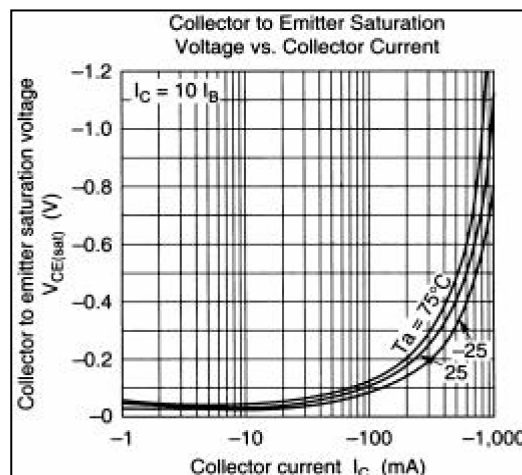
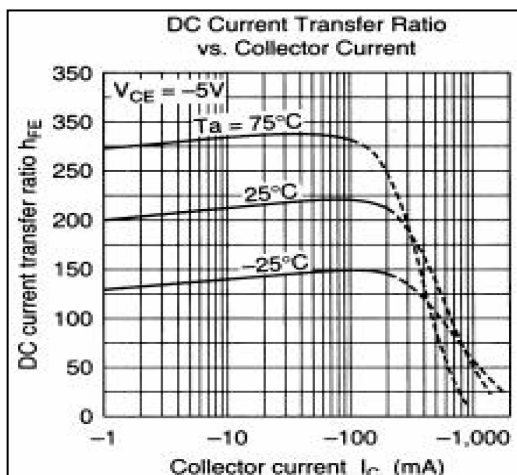
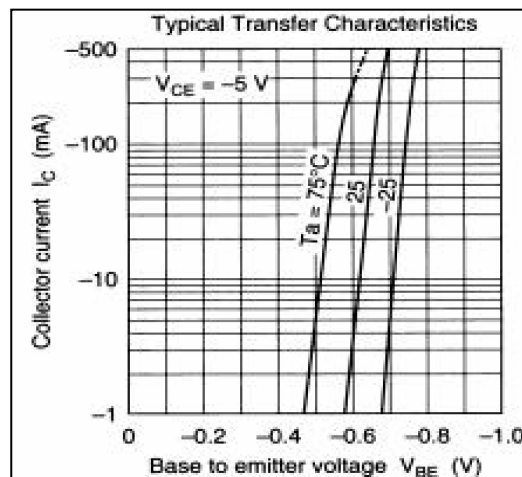
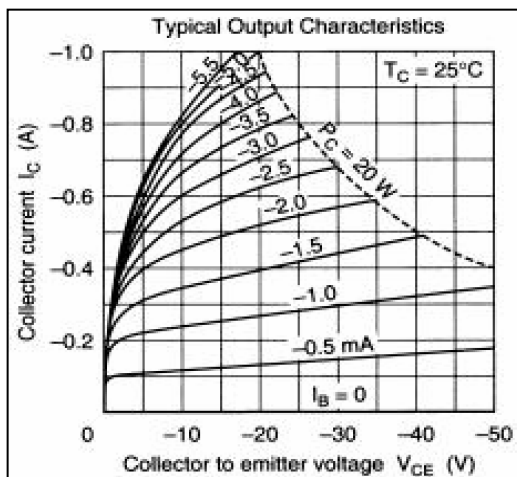
Classification Of hFE1

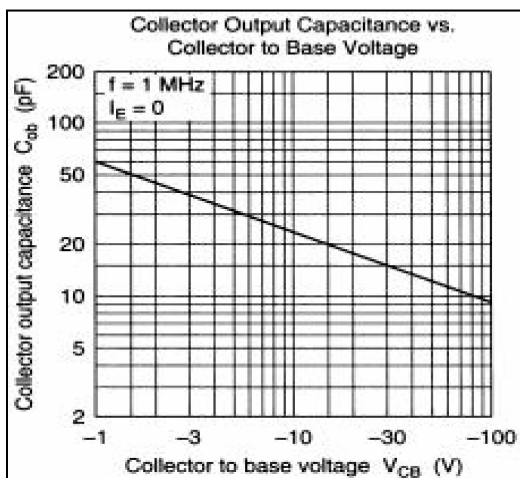
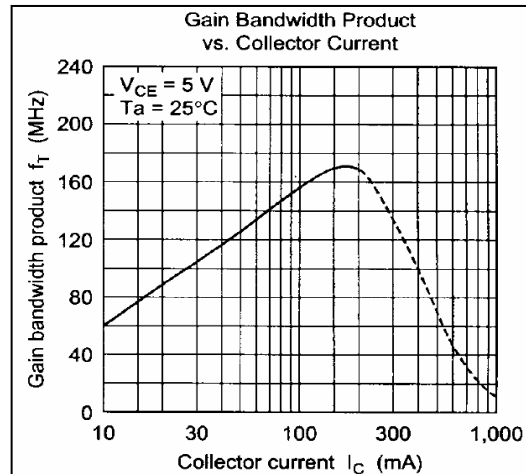
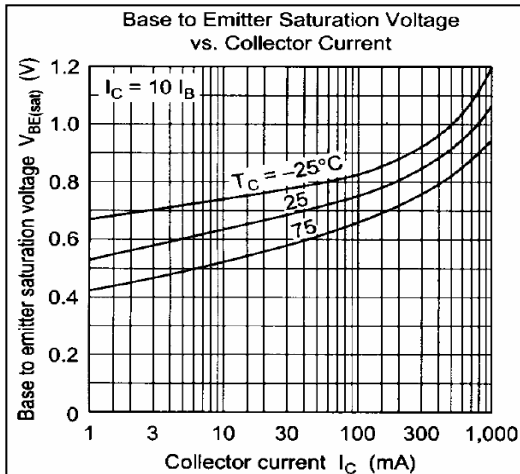
Rank	B	C
Range	60-120	100-200

Typical Parameters Performance



Characteristics Curve



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